

### General Description

The QM0020AP is the highest performance trench N-ch MOSFETs with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The QM0020AP meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

### Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

### Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	100	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^{1,7}$	128	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^{1,7}$	81	A
$I_D@T_A=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	11.2	A
$I_D@T_A=70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	9	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	310	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	550	mJ
$I_{AS}$	Avalanche Current	95.5	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation <sup>4</sup>	260	W
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation <sup>4</sup>	2.02	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

### Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	---	62	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	0.48	$^\circ\text{C/W}$

### Product Summary

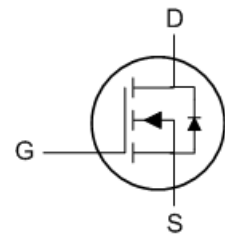
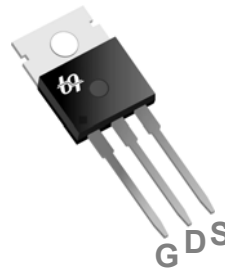


BVDSS	RDSON	ID
100V	8.5mΩ	128A

### Applications

- High Frequency Point-of-Load Synchronous Buck Converter
- Networking DC-DC Power System
- Power Tool Application

### TO220 Pin Configuration



**N-Ch 80V Fast Switching MOSFETs**
**Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	100	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	$BV_{DSS}$ Temperature Coefficient	Reference to $25^\circ\text{C}$ , $I_D=1\text{mA}$	---	0.128	---	V/ $^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=10V, I_D=30A$	---	7	8.5	m $\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	2.5	---	4.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5.9	---	mV/ $^\circ\text{C}$
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=80V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	$\mu A$
		$V_{DS}=80V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	5	
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	$\pm 100$	nA
$g_{fs}$	Forward Transconductance	$V_{DS}=5V, I_D=30A$	---	46	---	S
$R_g$	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	2.8	5.6	$\Omega$
$Q_g$	Total Gate Charge (10V)	$V_{DS}=80V, V_{GS}=10V, I_D=30A$	---	88	123	nC
$Q_{gs}$	Gate-Source Charge		---	41.5	58	
$Q_{gd}$	Gate-Drain Charge		---	14.7	20	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=50V, V_{GS}=10V, R_G=3.3\Omega, I_D=30A$	---	41	82	ns
$T_r$	Rise Time		---	59	106	
$T_{d(off)}$	Turn-Off Delay Time		---	51	102	
$T_f$	Fall Time		---	17.6	35	
$C_{iss}$	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1\text{MHz}$	---	7283	10196	pF
$C_{oss}$	Output Capacitance		---	1042	1458	
$C_{rss}$	Reverse Transfer Capacitance		---	249	348	

**Guaranteed Avalanche Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy <sup>5</sup>	$V_{DD}=50V, L=0.1\text{mH}, I_{AS}=30A$	54	---	---	mJ

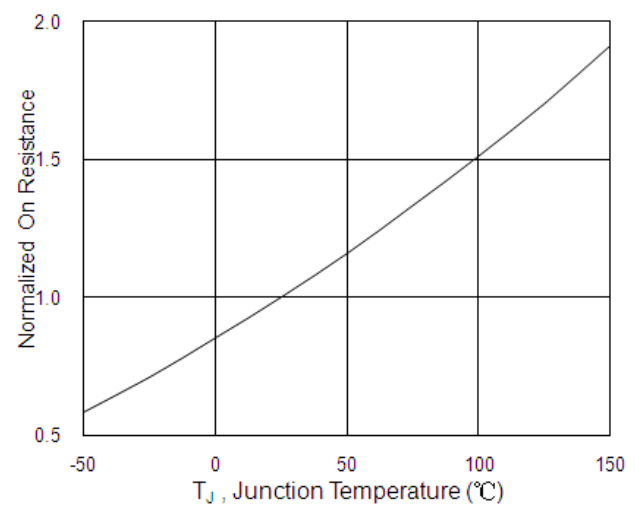
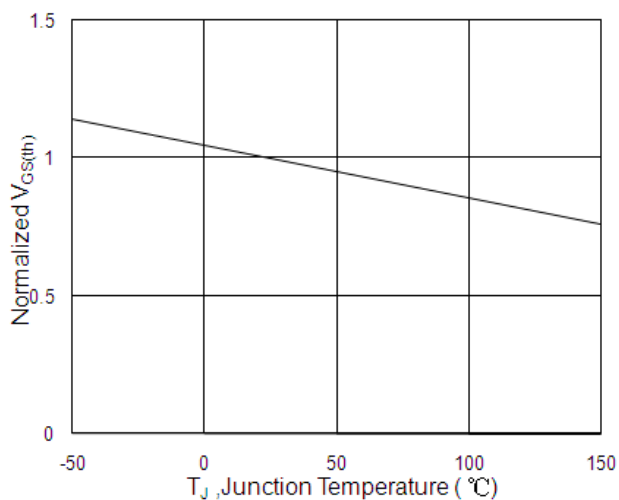
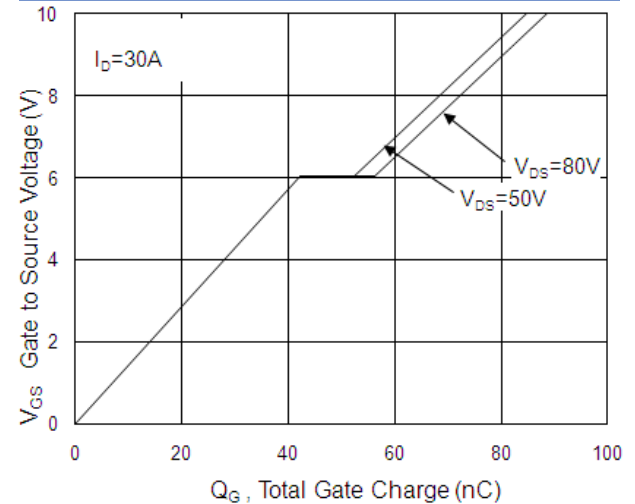
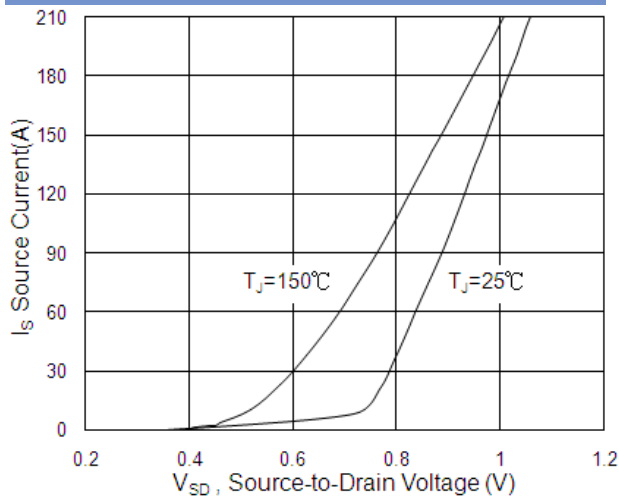
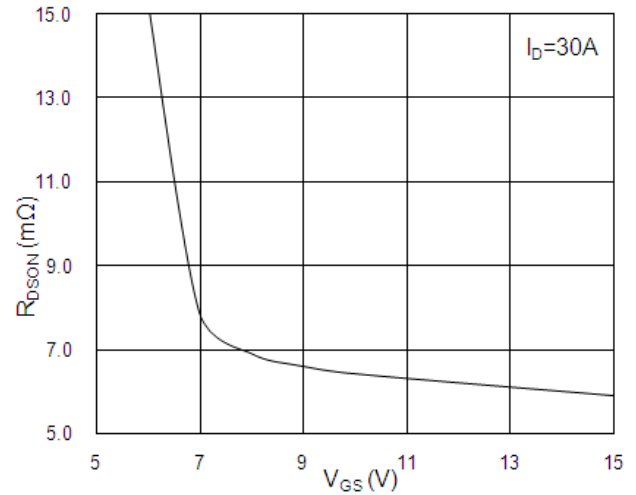
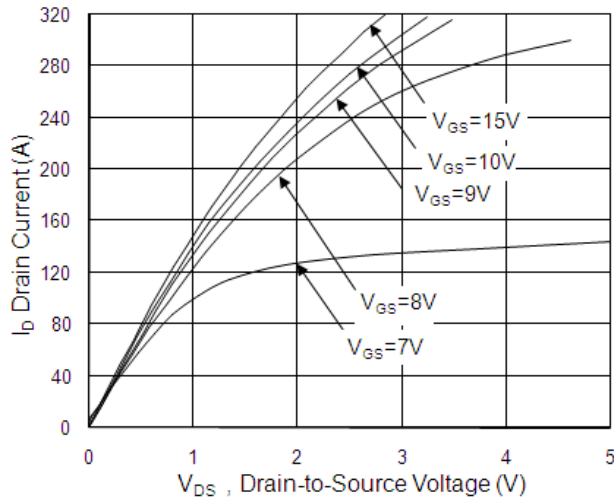
**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$I_S$	Continuous Source Current <sup>1,6</sup>	$V_G=V_D=0V$ , Force Current	---	---	128	A
$I_{SM}$	Pulsed Source Current <sup>2,6</sup>		---	---	310	A
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	$V_{GS}=0V, I_S=A, T_J=25^\circ\text{C}$	---	---	1.2	V
$t_{rr}$	Reverse Recovery Time	$I_F=30A, dI/dt=100A/\mu s, T_J=25^\circ\text{C}$	---	58	---	nS
$Q_{rr}$	Reverse Recovery Charge		---	134	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is  $V_{DD}=50V, V_{GS}=10V, L=0.1\text{mH}, I_{AS}=95.5A$
- 4.The power dissipation is limited by  $150^\circ\text{C}$  junction temperature
- 5.The Min. value is 100% EAS tested guarantee.
- 6.The data is theoretically the same as  $I_D$  and  $I_{DM}$ , in real applications , should be limited by total power dissipation.
- 7.Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 120A.

### Typical Characteristics



## N-Ch 80V Fast Switching MOSFETs

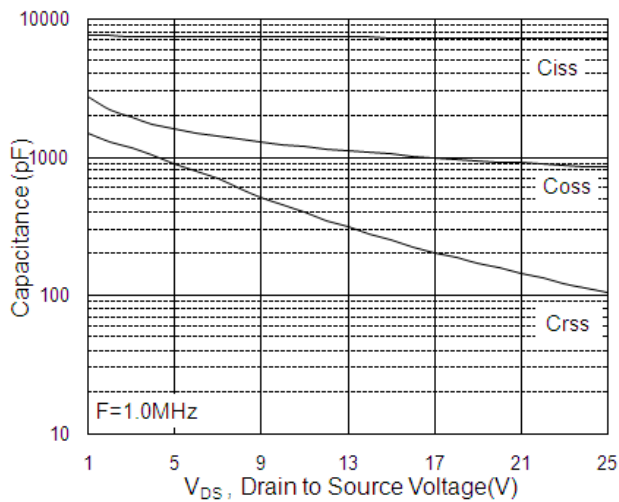


Fig.7 Capacitance

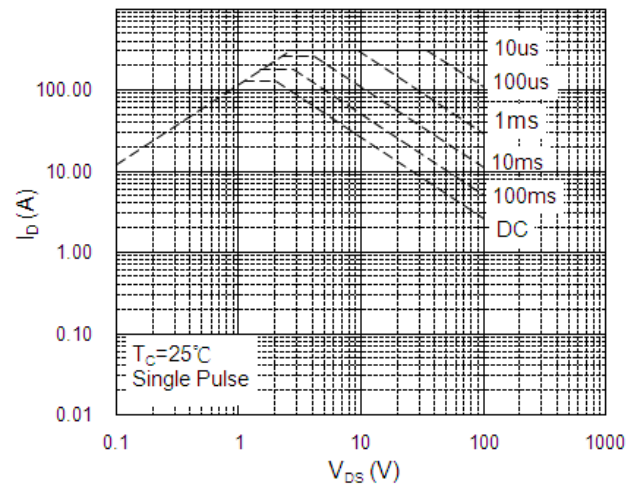


Fig.8 Safe Operating Area

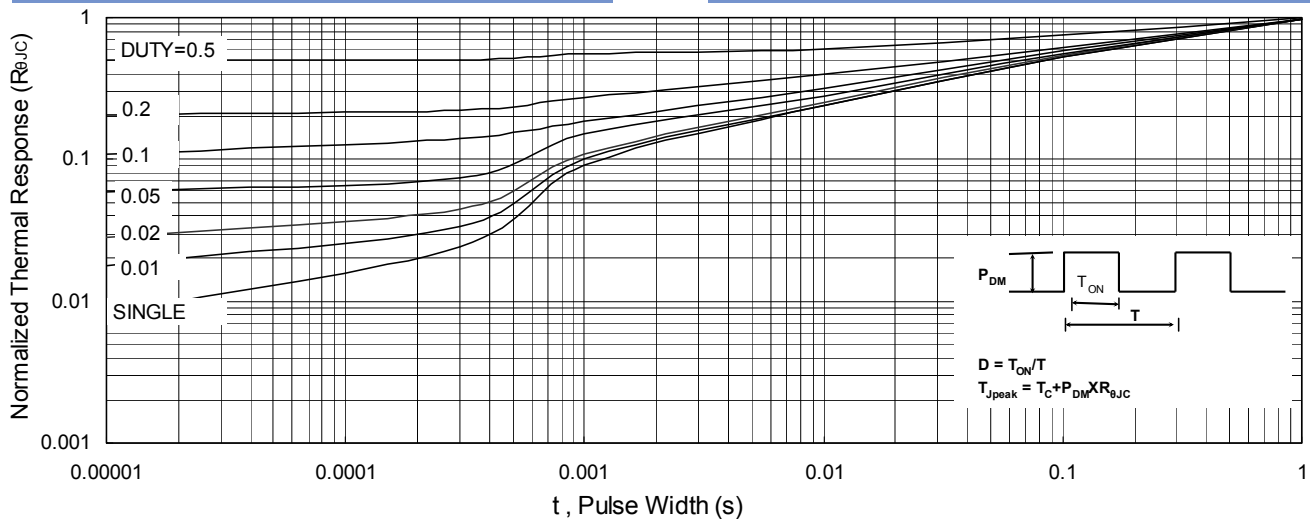


Fig.9 Normalized Maximum Transient Thermal Impedance

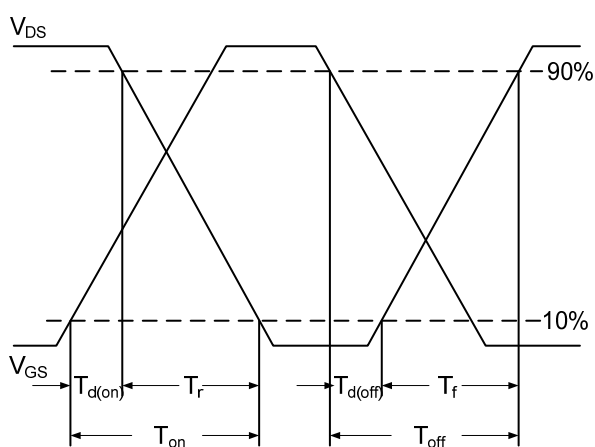


Fig.10 Switching Time Waveform

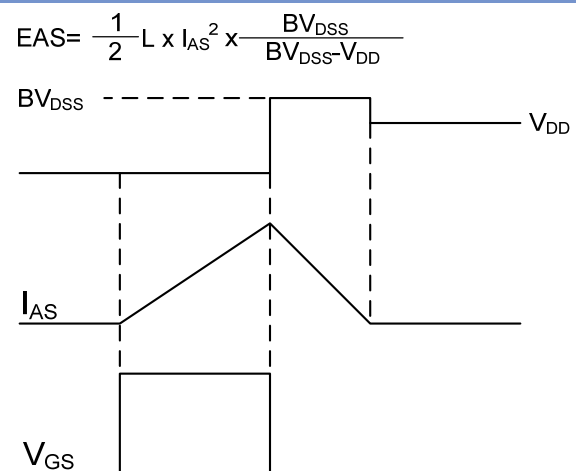


Fig.11 Unclamped Inductive Switching Waveform